The following listing of claims will replace all prior versions, and listings, of the claims in this application.

Listing of the claims:

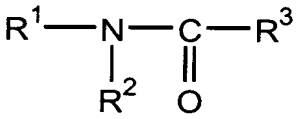
Claims 1-3 (Cancelled).

4. (Currently Amended) A chemically amplified resist composition, comprising

a resin which becomes soluble in an aqueous alkali solution in the presence of an acid,

a ~~photacid~~ photo acid generator, and

an amine derivative which shows, in water of 25°C, a basicity as to form a conjugate acid and has a medium polarity, wherein the amine derivative is an amide compound represented by formula (1):



(1)

wherein R^1, R^2 and R^3 are each independently hydrogen or an alkl group having from 1 to 30 carbon atoms, and wherein at least one of R^1 and R^2 is a cyclic alkyl group having 3 to 30 carbon atoms.

5. (Previously Presented) The chemically amplified resist composition according to Claim 4, wherein the amine derivative is a basic compound which forms a conjugate acid having a pKa of -3 to 3, in water of 25°C.

6. (Previously Presented) The chemically amplified resist composition according to Claim 4, wherein the amine derivative is a basic compound which has such a polarity as to give a water-octanol partition coefficient (Log P) of 0 to 1.5 at 25°C.

7. (Previously Presented) A chemically amplified resist composition comprising a resin soluble in an aqueous alkali solution in the presence of an acid, which is a polymer comprising a (meth)acrylic acid ester monomer unit having an alicyclic skeleton, and a (meth)acrylic acid ester monomer unit having a lactone skeleton;

a photo acid generator; and

an amine derivative which shows, in water of 25°C, a basicity as to form a conjugate acid and has a medium polarity.

8. (Previously Presented) The chemically amplified resist composition according to Claim 7, wherein the (meth)acrylic acid ester monomer unit having the alicyclic skeleton is at least one kind selected from the group consisting of cyclohexyl (meth)acrylate, isobornyl (meth)acrylate, adamantyl (meth)acrylate, tricyclodecanyl (meth)acrylate, dicyclopentadienyl (meth)acrylate, and their derivatives formed by introducing a substituent onto the alicyclic ring of the monomer unit.

9. (Previously Presented) The chemically amplified resist composition according to Claim 7, wherein the (meth)acrylic acid ester monomer unit having the lactone skeleton is at least one kind selected from the group consisting of (meth)acrylates having a δ-valerolactone ring, (meth)acrylates having a γ-butyrolactone ring, and their derivatives formed by introducing a substituent onto the lactone ring of the monomer unit.

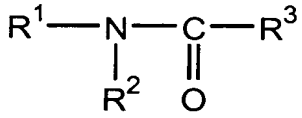
Claim 10 (Cancelled).

11. (Previously Presented) A chemically amplified resist composition which gives a line width difference between resist top and resist bottom, of 4% or less, in a resist pattern of 0.12 micron formed,

when the resist composition is coated on bare silicon to form a resist of 0.5 micron in thickness, a light of 193 nm emitted from an argon fluorine excimer laser is applied to the resist at an exposure of 5 mJ/cm^2 or less through a mask having a pattern of line/space = 1/1 to project the pattern to the resist in 1/4 reduction, and the resulting resist is heat-treated at 120°C for 60 seconds and subjected to development with a 2.38 mass % aqueous tetramethylammonium hydroxide solution of 23°C for 60 seconds.

12. (Previously Presented) The chemically amplified resist composition according to claim 4, wherein in formula (1), at least two of R^1, R^2 and R^3 bond to each other to form a cyclic skeleton.

13. (Previously Presented) The chemically amplified resist composition according to claim 7, wherein the amine derivative is an amide compound represented by formula (1):



(1)

wherein R^1, R^2 and R^3 are each independently hydrogen or an alkyl group having 1 to 30 carbon atoms.

14. (Previously Presented) The chemically amplified resist composition according to claim 13, wherein in formula (1), at least two of R^1, R^2 and R^3 bond to each other to form a cyclic skeleton.

15. (Previously Presented) The chemically amplified resist composition according to claim 13, wherein in formula (1), at least one of R^1 and R^2 is a cyclic alkyl group having 3 to 30 carbon atoms.

16. (Previously Presented) The chemically amplified resist composition according to claim 7, wherein the amine derivative is a basic compound which forms a conjugate acid having a pKa of -3 to 3, in water of 25°C.

17. (Previously Presented) The chemically amplified resist composition according to claim 7, wherein the amine derivative is a basic compound which has such a polarity as to give a water-octanol partition coefficient (Log P) of 0 to 1.5 at 25°C.